

Index

A

Absorption, 337, 569
 Activation energy of NTD Si:H, 563
 Advanced lithographic technology (E-beam, X-ray, Ion beam, Direct write systems, Photo-resists, Equipment), 662
 Ageing of wires, 468
 Air filtration systems, 163
 Amorphous layers, 661
 Anisotropic etching, 29
 Annealing, 77, 97, 105, 106, 204, 403, 460, 491, 560, 570, 590
 Antimony diffusion, 34
 Apodization function, 345
 Arsenic implantation, 65, 71
 Arsenic diffusion, 26, 34
 Artifact formation, 318
 Artifact transport, 179
 ASTM
 Committee F-1 on Electro-nics, 3, 10, 11, 12
 Fl21-80, 50
 Subcommittee Fl.07, 4
 Subcommittee Fl.10, 173
 Atomic level mechanisms, 32
 Autodoping, 38, 44
 Automation, 14
 Axial dopant distributions, 365
 Axial penning source, 78

B

Backside damage, 257, 324
 Backside scattering, 338
 Ball bonding, 429, 435
 Shearing, 430
 Testing of, 429
 Ball shear, 440, 448
 Ballistic transport, 35
 Bandgap, 33
 Base implant, 66
 Base sheet resistance, 69
 Base width, 24
 Beam geometry, 353
 Beryllium-doped gold wire, 486
 Beta, 70
 Beveling angle measurements, 285

Bipolar

 Epitaxy, 49-52
 ICs, 63
 Structure, 24, 25
 Transistors, 63
 Bonding, 429
 Ball, 429, 435
 Bumped tape, 512
 Horns, 472
 Innerlead, 513
 Interdependence of para-meters, 518, 524
 TAB, 500, 512
 Thermal shock, 517
 Thermocompression, 429, 472
 Ultrasonic, 458, 472
 Wire, 434, 458, 485
 Bonding horns, 472
 Bonding machine techniques, 513
 Bonding wire, 434, 458, 485
 Ageing, 468
 Fine wire, 458
 Mech. properties, 461, 488
 Book of Standards, 11
 Boron in silicon, 390, 409
 Channel implants, 22
 Diffusivity, 30, 31
 Implant, 30, 401, 409
 Borophosphosilicate glass, 358, 364
 Bragg reflection, 98
 Bulk
 Devices, 78
 Microdefects, 52, 60
 Stacking faults, 231, 235
 Bumped tape bonds, 513
 Buried layers, 40, 77

C

Capacitive bonder tuning, 472
 Capacitive microphone tuning, 473
 Capillary bonding tool, 481
 Carbon in silicon, 325
 Carrier continuity equation, 24
 Carrier lifetime, 658
 Channel length, 27
 Channel effects, 24
 Charge states, 32
 Classical implants, 88

666 SEMICONDUCTOR PROCESSING

- Clean rooms, 10
CMOS epitaxy, 49, 50
Co-diffusion, 69
Compressional sound waves, 473
Computer modeling, 21, 30, 66,
74, 391, 609
Container cleaning, 178
Contamination, 163, 172, 184, 443
Colloidal, 186
In bonding, 443
Ionic, 167
Levels, 173, 186
Metal, 241, 257, 272
Microbial, 167
Particulate, 164, 172, 196
Radiant energy, 170
Vibration, 170
Cooperative research, 647
University point-of-view,
648
Copper precipitates, 247
Crack theory, 278
Cross contamination, 266
Crystallinity, 102
C-V characteristics, 555
CVD oxide, 28
CVD system, 274
Cyclotron, 78
Czochralski crystal, 231
- D
- Damage due to implant, 77, 80
Damage profiles, 82-85, 88-91
Dark conductivity, 559
dB pressure level, 477
Dechanneling, 72, 75
Deep level transient spectroscopy, 543, 568
Defects, 243, 247, 283, 309,
566, 657
Defect delineation
Schimmel etch, 311
Seeco etch, 245
Sirtl etch, 309
Wright etch, 52, 208
Yang etch, 309
DLTS, 543, 568
Denudation, 50
Denuded cycle zone, 49, 50,
201, 209, 221, 232
Depth profile, 409
Detector-grade silicon, 542,
546
Detector, non-linearity, 344
Device
Isolation, 29
Modeling, 21, 24
Performance, 13
Problems, 24
Physics, 35
Reliability, 9, 12
Scaling, 26
Dichlorosilane, 38
Diffusion, 21, 30-32, 72
Antimony, 34
Arsenic, 26, 34
Base, 72
- Diffusion
Emitter, 72
Interstitial, 33
Phosphorus, 26
Dilute aluminum alloys, 458
DIN, 12
Diode C-V characteristics, 84
Direct write lithographic
system, 662
Dislocations, 32, 247
Doped poly, 26
Doping profile, distribution,
65, 81, 409
Dose vs generation rate, 87
Double crystal x-ray diffraction, 96, 97, 103, 104
Kinematical theory, 96-98
Drive-in, 65
Dry etching, 110
Using NF₃/Ar plasma, 110
Using NF₃/He plasma, 110
- E
- E-beam system, 127, 662
E-center, 77
Edge-controlled proximity
corrections, 124, 129
Electron-beam lithography, 124
Electron-pair generation, 90
Electron resist, 125
Electron spin resonance, 558
Electronic characterization,
557, 588
Electronics, 9
Electronic straggling, 92
Electrostatically-scanned ion
implanter, 64, 68, 72
Emission of particles, 81
Emitter dip effect, 223
Emitter transistor, 65, 66
Energy vs generation rate, 87
Enhanced precipitation, 52
Environmental control, 10, 11
Epitaxy, 11, 38, 49, 274, 325
Epitaxial deposition, 274
Rates, 41, 43
Epitaxial layer thickness, 11,
325
Equipotential contours, 26, 28
Etch & refill techniques, 28, 29
Evaluation of contamination,
172, 184
Oxide breakdown, 196
- Extinction length, 97
Extrinsic gettering, 257, 272
- F
- Fine wire, 458
Float-zone silicon, 365, 533,
546, 566, 595, 605, 615
Four-point probe, 11
Focal plane distributions, 151
Focal plane statistics, 149
Fracture Marking & Tracing, 298
FTIR measurements, 204, 231,
320, 325, 335, 345, 358, 567

G

Gain control, 63
 Gain in bipolar transistors, 63
 66, 68
 Gallium arsenide, 575, 587
 Gases, 13
 Gas phase doping, 39
 Gate arrays, 505
 Gate oxidation, 27
 Generation lifetime, 236
 Generation rate vs dose, 87
 Energy dependence, 87
 Germanium concentration, 272
 Gettering efficiency, 279, 659
 Gold gettering, 281
 Gold profile, 225, 228, 280
 Gorey-Schneider probe grinder,
 379, 394
 Guinier-Preston (GP) zone, 459

H

Hall measurements, 578, 589
 Haze, 659
 Haze/fog test, 257
 Hcl oxidation, 225
 Heavy metals, 257, 273
 He-Ne laser, 176
 Hiconex sputtering source, 78
 High energy implanter, 77
 High lead count, 507
 Horizontal reactors (epi), 44
 Hybrid bonding, 434
 Testing of, 429
 Hydrogenated amorphous NTD
 silicon, 558

I

ICs, 9, 13
 Implant
 Angle, 72
 Classical, 88
 Dose, 67
 In gallium arsenide, 77, 82
 In germanium, 77, 85
 In glass, 77, 81
 In silicon, 77, 85
 In quartz, 77
 With heavy ions, 78
 Implant species, 77
 Boron, 30, 401, 409
 Carbon, 77, 82
 Nitrogen, 77
 Noble gases (Ne, Kr,...),
 77, 80, 82, 90
 Oxygen, 77
 Phosphorus, 96, 102, 105
 Implanted thyristor, 84, 85
 Impurity diffusivity, 34
 Impurity profiles
 In channel regions, 23
 In field regions, 23
 Impurity segregation, 69
 Indium precipitates, 251
 Infrared measurements, 335,
 343

Institute of Environmental
 Sciences, 15

Interconnects, 458
 Interconnection technology, 502
 Interferometric patterns, 144
 Interlaboratory testing, 11, 15
 Interstitials, 31, 288
 Interstitial oxygen, 50, 201,
 235, 335
 Intrinsic getter cycle, 51
 Intrinsic implant, 73
 Intrinsic or internal gettering,
 50, 202, 222, 231, 238, 241,
 252
 Inversion layer, 22
 Ion beam angle, 69
 Ion beam lithographic system,
 662
 Ion channeling, 63, 72, 81, 587
 Ion etch system, 112
 Ion implantation, 63, 77, 660
 Amorphous layers, 661
 Tilting, 66
 Ion implanters, 66, 68
 Ionization profile, 90
 IR absorption, 569
 Iron precipitates, 247
 Irradiation of glass, 88
 Isochronal annealing, 570
 Isotropic etching, 29
 I-V characteristics, 26

J

JEDEC, 10

K

Kinematical theory
 Double crystal x-ray
 diffraction, 96-98

L

Large devices, 22, 36
 Lateral autodoping, 44, 46
 Lattice damage, 90
 Lattice disorder, 103
 Lattice strain (implant), 96,
 106, 107
 Leakage current, 90
 Lifetime, 11, 49, 55, 554, 571,
 658
 Generation, 236
 In epitaxial layers, 60
 Minority carrier, 49, 51,
 55, 59, 92, 236
 Light scattering devices, 176
 Lithographic equipment, 662
 Lithographic patterns, 125,
 130-134
 Lithography, 124, 662
 Liquid cleanliness, 174
 Local diffusivities, 35
 Local slope, 150, 151
 LOCOS isolation structures, 28
 Low temperature donors, 201
 LPCVD, 29

M

Magnetic Czochralski, 231
 Manufacturing efficiency, 9
 Matte finish, 483
 MCNC, 648
 Mechanical properties of wires, 461, 488
 Mechanical strength, silicon, 659
 Mechanically-scanned ion implanter, 64, 66
 Metal contamination, 241, 257, 272
 Metal precipitation, 241, 247
 Methylisobutyl ketone, 134
 Microdefect formation, 210
 Microdefects, 52, 60
 Microelectronic interconnects, 458
 Microphone probe, 475
 Microporous membrane, 188
 Microsampling, 325
 Mil specs, 12
 Military standards, 9, 10
 Minority carrier lifetime, 49, 51, 55, 59, 92, 554
 Of generation, 92
 Of recombination, 92
 Misfit dislocations, 272
 Modeling, 609
 Molecular diffusion, 32
 Monte-Carlo calculations, 77, 91, 125
 Monocrystalline implantation, 82
 MOS c-t measurements, 55, 58, 59
 MOS device operation, 24

N

NASA, 13
 National Bureau of Standards, 11
 Neutron activation analysis, 257
 Neutron depth profiling (NDP), 412, 661
 Neutron flux, 601, 608, 618
 Neutron flux equilization, 612
 Neutron irradiation, 533, 546, 559, 566, 575, 587, 595, 605, 615, 628
 Neutron transmutation doping (NTD), 533, 546, 558, 566, 575, 587, 595, 605, 615, 628
 NF₃, 111
 NF₃ /Ar plasma, 110
 NF₃ /He plasma, 110, 114
 Nickel precipitates, 249
 Nitrogen trifluoride, 111
 NMOS
 Device, 27
 Process, 23, 26
 N/N+ epi-layers, 51
 Nomarski microscope, 275
 Non-uniformities in implants, 68

N/P epi-layers, 52
 NTD gallium arsenide, 575, 587
 Annealing behavior, 590
 Electronic characterization 577, 588
 Hall measurements, 578, 589
 Photoluminescence, 578, 583, 591
 NTD reactor, 533, 559, 575, 587, 595, 605, 615, 628
 NTD silicon, 533, 546, 558, 566, 595, 605, 615, 628
 Annealing behavior, 560, 570
 Computer modeling, 609
 Crystal quality, 538
 C-V characteristics, 555
 Dark conductivity, 559
 Defects, 566
 Detector-grade, 542, 546
 Effects of hydrogen, 558, 566
 Electron spin resonance, 558
 Lifetime, 554, 571
 Market development, 534
 Maximum diameter, 539, 546, 615, 628
 Nuclear parameters, 595
 Overcompensation, 553
 Photoconductivity, 559
 Radial resistivity variation 550, 571, 605
 Total capacity, 595
 Upper resistivity limit, 540
 Nuclear reaction, 81
 Nucleation, 50, 220

O

OED, 30
 Off-line computer simulations, 143, 146
 Optical absorption, 77, 81, 88
 Optical analyzer, 88
 Optical reflectivity, 77, 89, 90
 OSFs, 223
 Outdiffusion, 40, 220
 Outgassing, 168
 Polymeric materials, 168
 Oxidation, 21, 30
 Oxidation-enhanced diffusion, 30, 106, 283, 286
 Oxidation-induced stacking faults, 223, 316
 Oxidation measurements, 320, 325, 343
 Effects of backside damage, 324
 Polarization effects, 353
 Oxidation rate, 27
 Oxide-isolated structure, 24
 Oxygen diffusivity, 221, 223
 Oxygen precipitation, 49, 50, 201, 211, 220, 232, 658

P

Packaging, 507

- Panel & workshop discussions,**
 647, 654, 657
Advanced lithographic technology, 662
Control of contaminants, 654
Cooperative research, 647
Interconnection technology,
 655
Ion implant, 660
Material and process-induced defects, 657
Participation in standards work,
 14, 15
Particles, 163
 Airbourne, 163
 Effect of electrostatic charge, 169
 Measurements of, 172
 Microbial, 167
 Migrating, 164, 165
 Surface, 165
 Viable, 167, 179
Particulate contamination, 9,
 11, 14
Particle profiles, 77
Passivation, 566
Phosphorus diffusion, 26
Phosphorus implant, 96, 102, 105
Phosphorus in silicon, 358, 364
Photoconductive decay, 11
Photoconductive measurements,
 560
Photoconductivity, 559
Photolithographic process
 -Off line computer simulations, 143, 146
Photoluminescence, 578, 583,
 591
Photoresist
 Etching, 120, 121
 Electron, 125
 PMMA, 125
 Positive, 120
 Technology, 662
PISCES program, 35
Planar channeling, 69
Plasma etching, 110
PMMA photoresist, 125
P-N junction, 84
POCl₃ doping, 22
Point contact diode, 378
Point defects, 37, 219, 283
 Interaction, 58
 Nucleation, 220
 Outdiffusion, 220
Point-of-use filtration, 184,
 191
Polarization effects, 353
Poly gate, 22
Polysilicon, 364
 Deposition, 24
 Arsenic-doped, 24
 Etching, 111, 113
 Oxidation, 27
Polymeric materials, 168
P/P+ epi-layers, 52
Positive photoresist, 120
Precipitate-defect clustures, 230
- Precipitates**
 Copper, 251
 Indium, 251
 Iron, 247
 Metal, 241, 251
 Nickel, 249
 Oxygen, 201, 211, 220, 232
Precipitation density profile,
 228
Pre-epitaxial bake, 39
Preferential etch, 309, 311
Process chemicals, 13
Process-induced defects, 232
Process modeling, 21, 30, 34
Process perturbation, 27
Production equipment, 14
Programs
 Bell Laboratories, 35
 Fielday, 35
 PISCES, 35
 SUPREM, 21, 30
Proximity effect, 124
Pull test, 429, 462
Pull strength, 527
Purity, 13
- Q**
- Quality**
 NTD silicon, 538
- R**
- RADC,** 13
Reactive ion etching, 110, 117
Reactor
 Advanced Test, 615, 628
 Design, 595, 605, 628
 Epitaxial, 21, 24, 36
 Heavy water, 605
 Horizontal hole, 595
 NTD, 533, 546, 559, 575,
 587, 595
Recombination velocity, 283
Reliability, 9, 12
Resists
 Electron, 125
 PMMA, 125
 Positive, 120
Resistivity measurements, 11
Retarded diffusion, 34
Reverse recovery charge, 93
Roles of Microelectronics Centers, 649
Round robin testing, 11
- S**
- Scaling,** 26
Secco etch, 245
Selective etching, 110
Selectivity, 112, 114, 121
SEMI, 10-13
Semiconductor quality, 9
Semiconductor Research Cooperative, 647
Semiconductor wire bonds, 429
 Testing of, 429

670 SEMICONDUCTOR PROCESSING

- Shadowing effect, 167
Shallow pits, 257
Shear test, 430
Shockley-Hall-Read statistics, 84
Shuttle tube irradiation, 634
Silicon/Silicon dioxide, 31
Silane deposition, 274
Silicate glasses, 358
Silicon
 Breakage, 297
 Czochralski, 231
 Dry etching, 110
 Epitaxial layers, 38, 49
 On heavily-doped substrates, 50
 Float zone, 365, 533, 546, 566, 595, 605, 615
 Magnetic Czochralski, 231
 Mechanical strength, 659
 Nitride, 22
 Oxide, 22, 110
 Phosphorus-doped, 22
 Thermal, 22
 Poly, 364
 Substrates, 9
 Silicon-on-sapphire, 401
 Silicon tetrachloride, 41, 44
SIMS, 66, 102, 208, 224, 272, 278, 390, 411, 661
Simulation, 21, 24, 28, 36, 66, 69, 74
Simulated spectra, 336
Single crystal growth, 26
Silicon oxide/nitride, 30
Silicon oxide precipitation, 50
Small VLSI devices, 24, 28, 30, 35, 36
 Channel effects, 24
 Electric fields in, 24
Source-drain implants, 22
Spatial manipulation, 148
Specifications, 9
Spreading resistance measurements, 375, 390, 411
 Effect of probe penetration 382
 Effect of rf radiation, 383
Spreading resistance technique-applications, 46, 77, 80, 84, 205, 551, 661
Stacking faults
 Bulk, 231, 235
 Oxygen-induced, 223, 316
Standard Reference Materials (SRM) program, 3, 10
Standards, 9-13
 Communications, 13
 Development, 9
 Types, 10
Stanford University, 28
Stepper simulations, 155
Strain, 32
 Distributions, 97, 99, 100, 101, 105
Sublimation effects, 83
Submicrometre contaminants, 172
 180
- Substrates, 9
Sub-threshold
 -currents, 26
 -region, 24
Super beta, 72
SUPREM, 21-23, 66, 69, 74, 391
Surface
 -contamination, 11
 -current, 86
 -films, 168
 -oxidation, 31
Swirl patterns, 315
- T
- Tape Automatic Bonding [TAB], 500, 512
TEM, 242, 274, 279
Testing equipment, 14
Thermal donors, 201
Thermal oxidation, 28, 29, 32
Thermosonic bonding, 429, 472
 Temperature effects, 445
Threshold voltage, 22, 27
Thyristors, 77, 84
Transistor structure
 -shallow emitter, 72
Traps, 32
Trench-like structures, 28
 Leakage currents in, 30
Trichlorosilane, 51
Two dimensional
 -kinetics, 34
 -process simulation, 35
 -structures, 35
- U
- Ultrafiltration, 187, 190
Ultrasonic bonding tool, 458, 472, 483
Ultrasonic power node, 472
University research, 648, 650
Upward diffusion, 24
- V
- Vacancies, 31, 32, 88, 290
 Energy level, 33
 Formation, 58
 Impurity, 33
Van de Graaff cyclotron, 78
Vertical pancake reactor, 38
Vibrations, 170
VICKSI accelerator, 78, 93
VLSI/VHSIC structures, 21, 501, 506
Volumetric sensor system, 177
- W
- Wafer
 -flatness, 143
 -fracture, 297
 -warpage, 236
Water, 184
Wet oxidation, 234
White room, 9

- Wire bond deformation, 479
Wire bonding, 434
 Testing of, 429
 Failure modes, 451
Workshop discussions, 654
 Control of contaminants, 654
 Interconnection Technology,
 655
Wright etch, 52, 208
- X
- XPS, 111, 116
X-ray
 -lithographic system, 662
- X-ray photoelectron spectroscopy
 111, 116, 121
 -rocking curves, 96, 97, 99
 100, 104
 -spectrometer, 242
- Y
- Yield enhancement, 144, 152
- Z
- Zero-dislocation crystals, 370
Zone refining, 365, 370
Zone length, 365, 368